

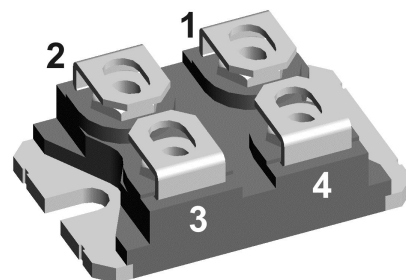
HiPerDynFRED

$$\begin{aligned} V_{RRM} &= 1800 \text{ V} \\ I_{FAV} &= 2 \times 25 \text{ A} \\ t_{rr} &= 30 \text{ ns} \end{aligned}$$

High Performance Dynamic Fast Recovery Diode
 Extreme Low Loss and Soft Recovery
 Parallel legs with series connected dice

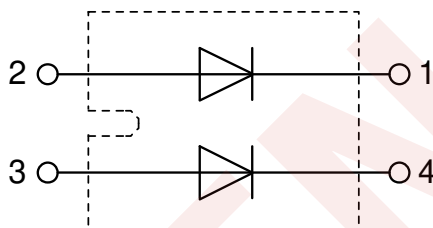
Part number

DPJ50XS1800NA



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

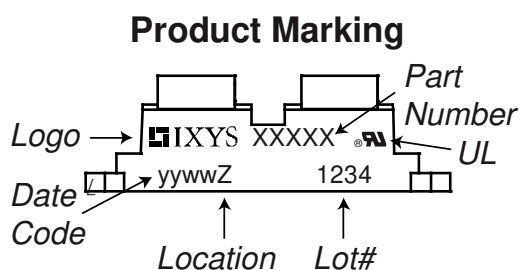
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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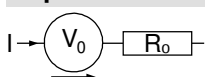
Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
I_R	reverse current, drain current	$V_R = 1800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			250	μA
		$V_R = 1800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 25\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			6.99	V
		$I_F = 50\text{ A}$				8.72	V
		$I_F = 25\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			4.33	V
		$I_F = 50\text{ A}$				5.83	V
I_{FAV}	average forward current	$T_C = 90^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			25	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		2.92	V
r_F	slope resistance					56	m Ω
R_{thJC}	thermal resistance junction to case					0.4	K/W
R_{thCH}	thermal resistance case to heatsink				0.1		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				315	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			250	A
C_J	junction capacitance	$V_R = 900\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		10		pF
I_{RM}	max. reverse recovery current	} $I_F = 30\text{ A}; V_R = 900\text{ V}$ $-di_F/dt = 400\text{ A}/\mu\text{s}$		$T_{VJ} = 25^{\circ}\text{C}$		9	A
				$T_{VJ} = 125^{\circ}\text{C}$		13	A
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		30	ns
				$T_{VJ} = 125^{\circ}\text{C}$		140	ns

Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				100	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		150	°C
Weight					30		g
M_D	mounting torque			1.1		1.5	Nm
M_T	terminal torque			1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2			mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V
		t = 1 minute		2500			V


Part description

D = Diode
 P = HiPerFRED
 J = HiPerDyn +
 50 = Current Rating [A]
 XS = Parallel legs with series connected dice
 1800 = Reverse Voltage [V]
 NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPJ50XS1800NA	DPJ50XS1800NA	Tube	10	517619

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 150^{\circ}\text{C}$

 $V_{0\max}$ threshold voltage

Fast Diode

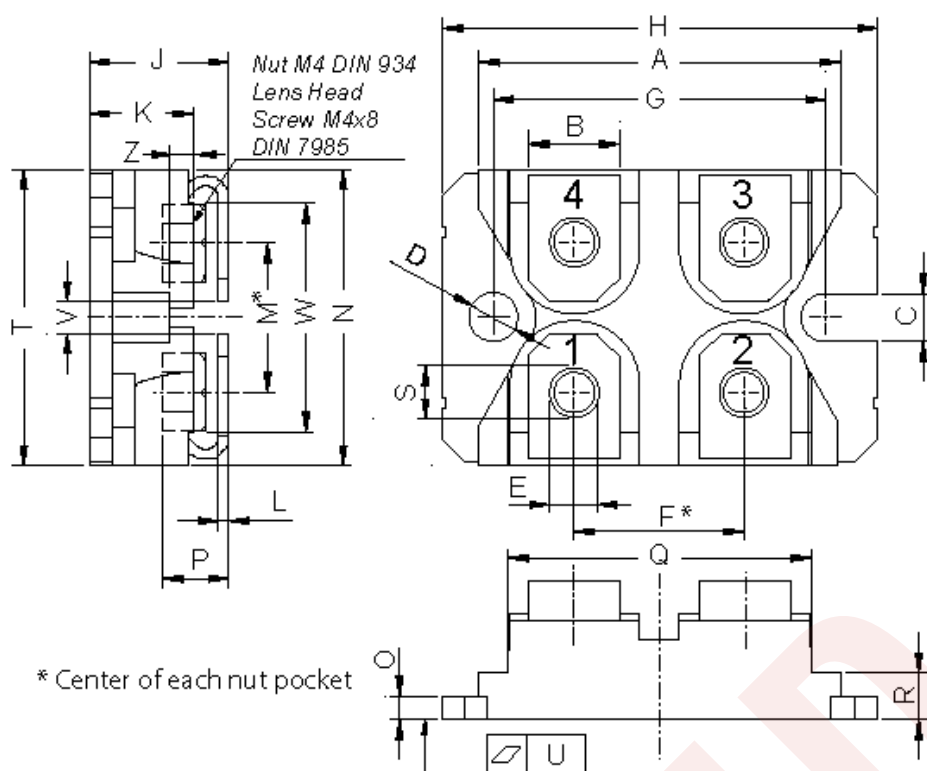
2.92

V

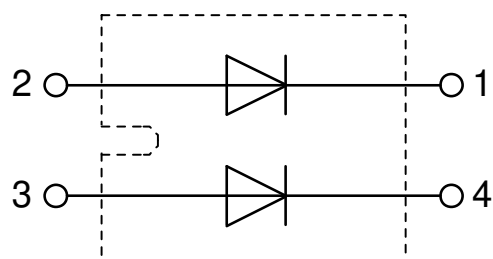
 $R_{0\max}$ slope resistance *

55

mΩ

Outlines SOT-227B (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



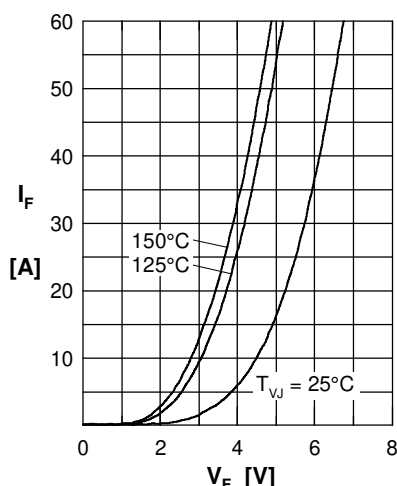
Fast Diode


Fig. 1 Typ. Forward current I_F versus V_F

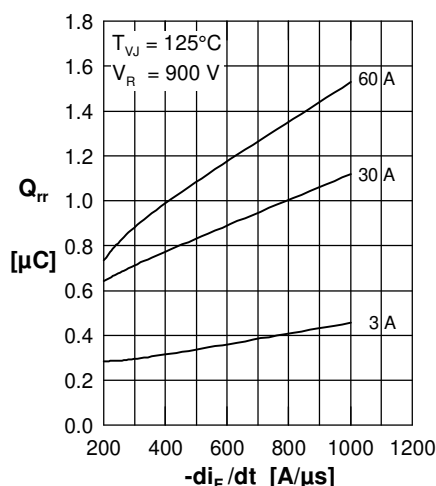


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

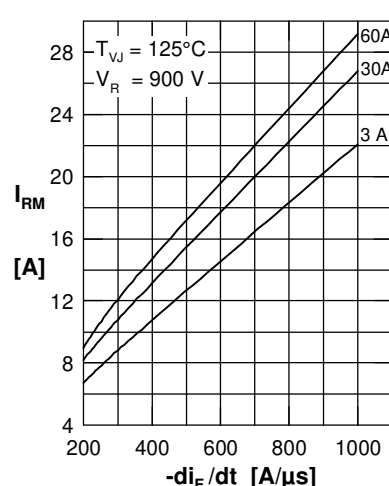


Fig. 3 Typ. reverse recov. current I_{RM} versus $-di_F/dt$

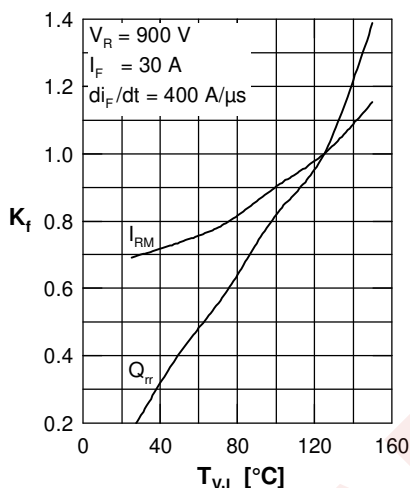


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

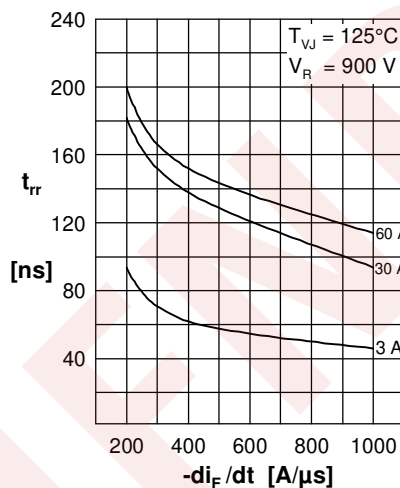


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

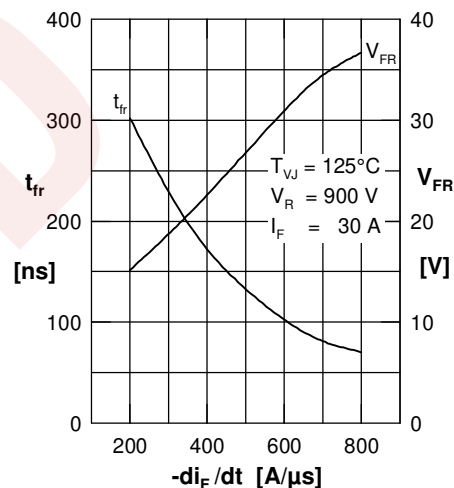


Fig. 6 Typ. forward recov. voltage V_{FR} & time t_{fr} versus di_F/dt

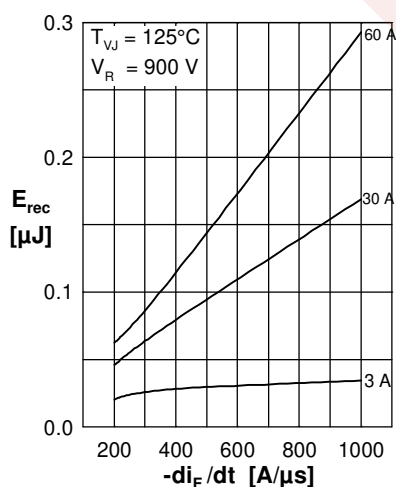


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

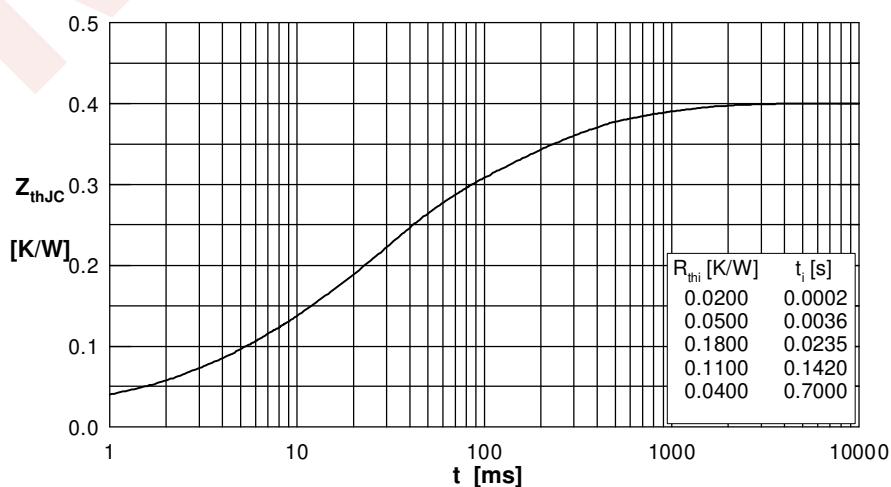


Fig. 8 Transient thermal impedance junction to case